1 637 migrat\$3 with etch\$3 USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; and (thin near film near transistor) US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT USPAT USPAT USPAT 2003 ((438/149) or (438/479)).CCLS.	e stamp /06/05 16:1: 9/06/05 16:1:	.3
US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT USPAT 2003 ((438/149) or (438/479) or (438/517) or (438/149) or (438/479) or (438/476) or (438/486) or (438/487) or (438/491).CCLS.	/06/05 16:1	٦
EPO; JPO; DERWENT; IBM_TDB 2 429 (migrat\$3 with etch\$3) and semiconductor USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB 3 13 ((migrat\$3 with etch\$3) and semiconductor) USPAT; USPAT; USPAT; USPAT; USPAT and (thin near film near transistor) USPAT; USPAT - 459 ((438/149) or (438/479)).CCLS. 1277 ((438/149) or (438/479) or (438/517) or (438/151) or (438/473) or (438/476) or (438/486) or (438/487) or (438/491)).CCLS. - 139 ((("438/149") or ("438/479") or ("438/517") USPAT 2000		
DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT USPAT USPAT 2003 13 ((438/149) or (438/479)).CCLS. 1277 ((438/149) or (438/479) or (438/517) or (438/151) or (438/473) or (438/476) or (438/486) or (438/487) or (438/491)).CCLS. 139 ((("438/149") or ("438/479") or ("438/517") USPAT 2000		
2 429 (migrat\$3 with etch\$3) and semiconductor USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB 3 13 ((migrat\$3 with etch\$3) and semiconductor) USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB 459 ((438/149) or (438/479)).CCLS. - 459 ((438/149) or (438/479)).CCLS. 1277 ((438/149) or (438/479) or (438/517) or (438/517) or (438/517) or (438/486) or (438/487) or (438/491)).CCLS. - 139 ((("438/149") or ("438/479") or ("438/517") USPAT 2000		
2 429 (migrat\$3 with etch\$3) and semiconductor USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB 3 13 ((migrat\$3 with etch\$3) and semiconductor) USPAT; US-PGPUB; and (thin near film near transistor) USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB - 459 ((438/149) or (438/479)).CCLS 1277 ((438/149) or (438/479) or (438/517) or (438/151) or (438/473) or (438/476) or (438/486) or (438/487) or (438/491)).CCLS 139 ((("438/149") or ("438/479") or ("438/517") USPAT 2000		
US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; 2003 US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT 2003 1277 ((438/149) or (438/479)).CCLS. USPAT 2003 USPAT 2003 USPAT 2003 USPAT 2003 (438/151) or (438/479) or (438/517) or (438/151) or (438/479) or (438/476) or (438/486) or (438/487) or (438/4791).CCLS.		2
EPO; JPO; DERWENT; IBM_TDB USPAT; and (thin near film near transistor) - 459 ((438/149) or (438/479)).CCLS 1277 ((438/149) or (438/479) or (438/517) or (438/151) or (438/486) or (438/487) or (438/491)).CCLS 139 ((("438/149") or ("438/479") or ("438/517") USPAT 2000	/06/05 16:1	٦
DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT U	/06/05 16:1	
3 13 ((migrat\$3 with etch\$3) and semiconductor) and (thin near film near transistor) US-PGPUB; EPO; JPO; DERWENT; IBM_TDB - 459 ((438/149) or (438/479)).CCLS 1277 ((438/149) or (438/479) or (438/517) or (438/151) or (438/473) or (438/476) or (438/486) or (438/487) or (438/491)).CCLS 139 ((("438/149") or ("438/479") or ("438/517") USPAT 2000	7/06/05 16:1	
3 13 ((migrat\$3 with etch\$3) and semiconductor) and (thin near film near transistor) USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB - 459 ((438/149) or (438/479)).CCLS. USPAT 2003 - 1277 ((438/149) or (438/479) or (438/517) or (438/151) or (438/473) or (438/476) or (438/486) or (438/487) or (438/491)).CCLS. - 139 ((("438/149") or ("438/479") or ("438/517") USPAT 2000	/06/05 16:1	
and (thin near film near transistor) - 459 ((438/149) or (438/479)).CCLS 1277 ((438/149) or (438/479) or (438/517) or (438/151) or (438/473) or (438/476) or (438/486) or (438/487) or (438/491)).CCLS 139 ((("438/149") or ("438/479") or ("438/517") USPAT 2000		4
DERWENT; IBM_TDB USPAT 2003 1277 ((438/149) or (438/479)).CCLS. (438/151) or (438/479) or (438/476) or (438/486) or (438/487) or (438/491)).CCLS. (438/151) or (438/487) or (438/491)).CCLS. 139 ((("438/149") or ("438/479") or ("438/517") USPAT 2000		ł
- 459 ((438/149) or (438/479)).CCLS.		
- 459 ((438/149) or (438/479)).CCLS. USPAT 2003 - 1277 ((438/149) or (438/479) or (438/517) or USPAT 2000 (438/151) or (438/473) or (438/476) or (438/486) or (438/487) or (438/491)).CCLS. - 139 ((("438/149") or ("438/479") or ("438/517") USPAT 2000		
- 1277 ((438/149) or (438/479) or (438/517) or USPAT 2000 (438/151) or (438/473) or (438/476) or (438/486) or (438/487) or (438/491)).CCLS 139 ((("438/149") or ("438/479") or ("438/517") USPAT 2000		
(438/151) or (438/473) or (438/476) or (438/486) or (438/487) or (438/491)).CCLS. - 139 ((("438/149") or ("438/479") or ("438/517") USPAT 2000	/06/05 16:1	.3
(438/486) or (438/487) or (438/491)).CCLS. - 139 ((("438/149") or ("438/479") or ("438/517") USPAT 2000	/09/21 14:3	
- 139 ((("438/149") or ("438/479") or ("438/517") USPAT 2000		
	/09/21 14:3:	9
or ("438/486") or ("438/487") or		
("438/491")).CCLS.) and (nickle or Ni)		į
	0/09/21 14:3	9
or ("438/151") or ("438/473") or ("438/476")		1
or ("438/486") or ("438/487") or		
("438/491")).CCLS.) and (nickle or Ni)) and		
(irradiat\$)		
	0/09/22 08:5	5
("438/517") or ("438/151") or ("438/473") or		
("438/476") or ("438/486") or ("438/487") or		i
("438/491")).CCLS.) and (nickle or Ni)) and		
(irradiat\$)) and (phosph\$)	/05/55 55 =	_
- 4 (("5594569") or ("5643826") or ("5923962") USPAT 2000 or ("5854096")).PN.	0/09/22 09:5	6
	/00/22 00 5	_
	0/09/22 09:5	
and getter\$	0/09/22 09:5	′
	0/09/22 09:5	
and phosphor\$	/03/22 03:5	٥
	0/09/22 09:5	۵
and (TFT or (thin adj flim adj transistor))	/09/22 09.5	,
	/09/22 10:0	ا م
and (TFT or (thin adj flim adj transistor)))	/05/22 10.0	٠,
and method		i
	/09/22 10:00	0
and (TFT or (thin adj flim adj transistor)))	,, 10.0	-
and method) and phosphor\$		
	/09/22 11:0	5
JPO;		1
IBM_TDB		- 1
	/09/22 11:0	5
JPO;	-	
IBM TDB		ı
- 47 (((yamazaki adj shunpei).in.) and nickel) USPAT; 2000	/09/22 11:00	6
and getter\$ JPO;		
IBM_TDB		- [
	/09/22 11:0	8
and getter\$) and phosphor\$ JPO;		
IBM_TDB		
	/09/22 12:3	
	/09/22 12:3	
- 9 (("5854096") or ("5712191") or ("5696386") USPAT 2000	/09/25 13:3	1
or ("5960323") or ("5643826") or ("6093937")		
or ("6121076") or ("5616506") or		
("5888857")).PN.	104/35 33 3	_ ا
- 2 (("5594569") or ("5923962")).PN. USPAT 2001	/04/16 08:42	<u> </u>

-	0	(Ni or nickel or metal) with (UV or	USPAT;	2001/04/16 08:43
	İ	ultraviolet or IR or infrared) with	US-PGPUB;	
ļ		(amorphous adj silicon) with TFT	EPO; JPO;	
1			DERWENT;	
	41	(Ni or nickel or metal) with (UV or	IBM_TDB USPAT:	2001/04/16 08:43
-	41	ultraviolet or IR or infrared) with	US-PGPUB;	2001/04/16 08:43
		(amorphous adj silicon)	EPO; JPO;	
		(amorphous adj biricon)	DERWENT;	
			IBM TDB	
_	13	(Ni or nickel or metal) with (UV or	USPAT;	2001/04/16 08:50
		ultraviolet or IR or infrared) with	US-PGPUB;	
		(amorphous adj silicon) and TFT	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	81	TFT and (Si adj Ge)	USPAT;	2001/04/16 08:50
			US-PGPUB;	#II.
			EPO; JPO;	İ
			DERWENT; IBM TDB	
	37	(TFT and (Si adj Ge)) and Ni	USPAT;	2001/04/16 08:59
		(111 and (51 ad) (67) and WI	US-PGPUB;	2001,01,10 00.33
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	27		USPAT;	2001/04/16 09:03
		or ultraviolet or infrared)	US-PGPUB;	
			EPO; JPO;	1
			DERWENT;	
			IBM_TDB	2007/04/16 00 03
-	114	TFT and SiGe	USPAT;	2001/04/16 09:03
			US-PGPUB; EPO; JPO;	
1			DERWENT;	
			IBM TDB	
_	20	(TFT and SiGe) and Ni	USPAT;	2001/04/16 09:04
		(III and 5255) and III	US-PGPUB;	,,
			EPO; JPO;	·
			DERWENT;	
			IBM_TDB	
-	40	(TFT and SiGe) and (UV or IR or ultraviolet	USPAT;	2001/04/16 09:04
		or infrared)	US-PGPUB;	
			EPO; JPO;]
			DERWENT;	
	15	((TFT and SiGe) and Ni) and (UV or IR or	USPAT;	2001/04/16 09:07
•		ultraviolet or infrared)	US-PGPUB;	2002, 00, 20
1			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	11	TFT with SiGe	USPAT;	2001/04/16 09:07
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		(#6002027#) DN	IBM_TDB USPAT	2001/04/16 12:57
1.	1 4	("6093937").PN. ("5569610").PN.	USPAT;	2001/04/16 12:37
] -	4	1 33390IO /.EM.	US-PGPUB;	-552, -5, 15 15.17
			EPO; JPO;	
			DERWENT	
-	0	(peabody).at.	USPAT;	2001/10/10 16:17
		-	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		L	IBM_TDB	2001/10/10 15 15
-	893	(peabody).att.	USPAT;	2001/10/10 16:17
1	†		US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
1 -	796	(yamazaki adj shunpei).in.	USPAT	2001/10/10 16:19
-		Freidman.att.	USPAT	2001/10/10 16:19
<u> </u>	<u> </u>			

			7	
-	9412	(fish with richardson).att.	USPAT	2001/10/10 16:19
-	0	((fish with richardson).att.) and	USPAT	2001/10/10 16:21
		((semiconductor adj energy adj lab).as.)		
-	217	((fish with richardson).att.) and	USPAT	2001/10/10 16:22
		((semiconductor adj energy adj		
	}	laboratory).as.)		
-	29	(((fish with richardson).att.) and	USPAT	2001/10/11 08:59
		((semiconductor adj energy adj		
		laboratory).as.)) and (catalytic and laser)		
-	1	Freidman.att. and (catalytic and laser)	USPAT	2001/10/10 16:22
-	36		USPAT	2001/10/11 08:48
-	9	((peabody).att.) and (catalytic and laser)	USPAT	2001/10/11 09:04
		and (remove with oxide)		,
-	0	((peabody).att.) and (catalytic and laser)	USPAT	2001/10/11 08:57
		and (remove with oxide) and levling		
_	0	(USPAT	2001/10/11 08:58
		and (remove with oxide) and leveling		
-	0	· · · · · · · · · · · · · · · · · · ·	USPAT	2001/10/11 08:59
		and (remove with oxide) and planarize		
-	3	((USPAT	2001/10/11 08:59
		((semiconductor adj energy adj		l
		laboratory).as.)) and (catalytic and laser)		
	-	and (planarize or leveling or flatten or	i	
	}	smoothen)		
-	1	((peabody).att.) and (catalytic and laser)	USPAT	2001/10/11 09:05
	1	and (remove with oxide) and ((planarize or		
		planarization or planarized or flat or		
		flatten or flaten or flattened or leveling		
		or level or smooth or smoothen) with (heat		[
		or thermal or heated or heating))		
1 -	52	TFT and (laser with (air or oxygen) with	USPAT;	2002/05/31 09:11
		(crystallization or crystallized or	US-PGPUB;	
		crystalized or crystal))	EPO; JPO;	
			DERWENT;	
	1	mem and (lease with (also) with	IBM_TDB	2002/05/22 22 22
-	18		USPAT;	2002/05/31 09:12
		(crystallization or crystallized or	US-PGPUB;	
		crystalized or crystal))	EPO; JPO; DERWENT;	
L		<u> </u>	IBM_TDB	l